



**17.5V NPN MEDIUM POWER HIGH GAIN TRANSISTOR IN SOT223** 

#### **Features**

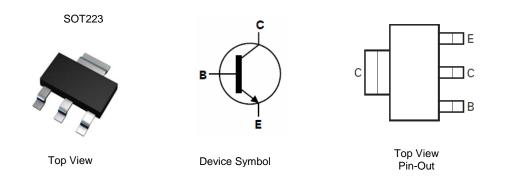
- BV<sub>CEO</sub> > 17.5V
- BV<sub>CES</sub> > 50V
- I<sub>C</sub> = 5A High Continuous Collector Current
- I<sub>CM</sub> = 20A Peak Pulse Current
- Low Saturation Voltage V<sub>CE(sat)</sub> <45mV @ 500mA</li>
- $R_{SAT} = 50m\Omega @ 5A$  for a Low Equivalent On-Resistance
- h<sub>FE</sub> Specified up to 20A for a High Gain Hold-Up
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads.
  Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.112 grams (Approximate)

#### Applications

- Solenoid, Relay and Actuator Drivers
- DC Modules
- Motor Control



### Ordering Information (Note 4)

	Product	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel	
	FZT1048ATA	FZT1048A	7	12	1,000	
Notes: 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.						

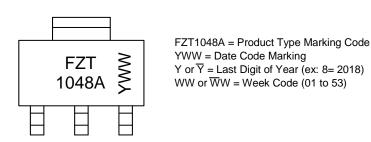
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied. 2. See http://www.diodes.com/quality/lead\_free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"

and Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

### **Marking Information**

SOT223





# Absolute Maximum Ratings ( $@T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	50	V
Collector-Emitter Voltage	V <sub>CEO</sub>	17.5	V
Emitter-Base Voltage	V <sub>EBO</sub>	7	V
Continuous Collector Current	Ι <sub>C</sub>	5	A
Peak Pulse Current	Ісм	20	A
Base Current	IB	500	mA

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		3.0		
Power Dissipation	(Note 6)	D-	2.0	W	
Power Dissipation	(Note 7)	PD	1.6		
	(Note 8)		1.2		
	(Note 5)		41.7		
Thermal Desistance, Junction to Ambient	(Note 6)	P	62.5		
Thermal Resistance, Junction to Ambient	(Note 7)	R <sub>0JA</sub>	78.1	°C/W	
	(Note 8)		104		
Thermal Resistance Junction to Lead (Note 9)		$R_{ ext{ heta}JL}$	10.9		
Operating and Storage Temperature Range	T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C		

## ESD Ratings (Note 10)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	ЗA
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes: 5. For a device mounted with the collector lead on 52mm x 52mm 2oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.

- Same as note (5), except the device is mounted on 25mm x 25mm 2oz copper.
- Same as note (5), except the device is mounted on 25mm x 25mm 202 copper.
  Same as note (5), except the device is mounted on 25mm x 25mm 1oz copper.

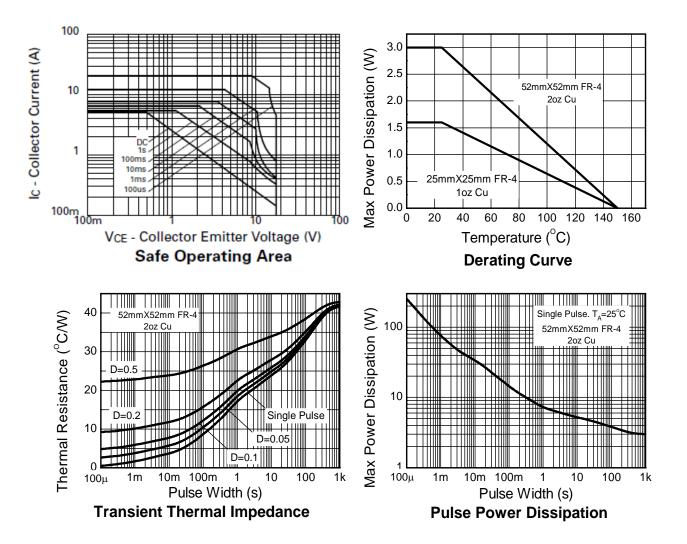
8. Same as note (5), except the device is mounted on minimum recommended pad layout.

9. Thermal resistance from junction to solder-point (at the end of the collector lead).

10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



# **Thermal Characteristics and Derating Information**





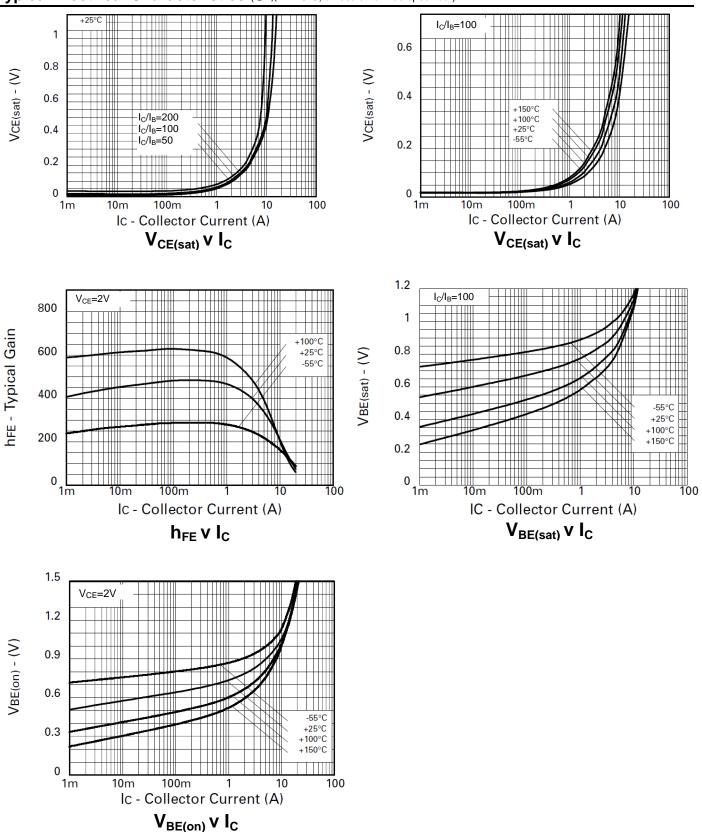
## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	50	85	—	V	I <sub>C</sub> = 100μA
Collector-Emitter Breakdown Voltage	BV <sub>CES</sub>	50	85	_	V	I <sub>C</sub> = 100μA
Collector-Emitter Breakdown Voltage	BV <sub>CEV</sub>	50	85	_	V	$I_{C} = 100 \mu A, V_{EB} = 1 V$
Collector-Emitter Breakdown Voltage (Note 11)	BVCEO	17.5	24	_	V	I <sub>C</sub> = 10mA
Emitter-Base Breakdown Voltage	BVEBO	7	8.7	_	V	I <sub>E</sub> = 100μA
Collector Cut-off Current	I <sub>CBO</sub>	_	0.3	10	nA	V <sub>CB</sub> = 35V
Collector Cut-off Current	ICES	_	0.3	10	nA	V <sub>CB</sub> = 35V
Emitter Cut-off Current	I <sub>EBO</sub>	_	0.3	10	nA	$V_{EB} = 4V$
		_	27	45	mV	I <sub>C</sub> = 500mA, I <sub>B</sub> = 10mA
Collector Freitter Coturction Mathema (Nate 44)	N/	_	55	75		$I_{C} = 1A, I_{B} = 10mA$
Collector-Emitter Saturation Voltage (Note 11)	V <sub>CE(sat)</sub>	_	155	210		$I_{\rm C} = 3A, I_{\rm B} = 15mA$
		_	250	350		$I_{\rm C} = 5$ A, $I_{\rm B} = 25$ mA
Base-Emitter Saturation Voltage (Note 11)	V <sub>BE(sat)</sub>	—	920	1,000	mV	I <sub>C</sub> = 5A, I <sub>B</sub> = 25mA
Base-Emitter Turn-On Voltage (Note 11)	V <sub>BE(on)</sub>	—	880	970	mV	$I_{C} = 5A, V_{CE} = 2V$
	h <sub>FE</sub>	280	440	—		$I_{C} = 10 \text{mA}, V_{CE} = 2 \text{V}$
		300	450	_		$I_{C} = 0.5A, V_{CE} = 2V$
DC Current Gain (Note 11)		300	450	1,200		$I_C = 1A, V_{CE} = 2V$
		180	300	—		$I_C = 5A, V_{CE} = 2V$
		50	80	—		$I_{C} = 20A, V_{CE} = 2V$
Output Capacitance	C <sub>obo</sub>	_	60	80	pF	V <sub>CB</sub> = 10V, f = 1MHz
Current Gain-Bandwidth Product	f <sub>T</sub>	_	150	_	MHz	$V_{CE} = 10V, I_C = 50mA,$ f = 50MHz
Switching Times	t <sub>on</sub>	—	120	—		$I_{C} = 4A, V_{CC} = 10V,$
Switching Times	t <sub>off</sub>	_	310	_	ns	$I_{B1} = -I_{B2} = 40 \text{mA}$

Note: 11. Measured under pulsed conditions. Pulse width  $\leq$  300µs. Duty cycle  $\leq$  2.



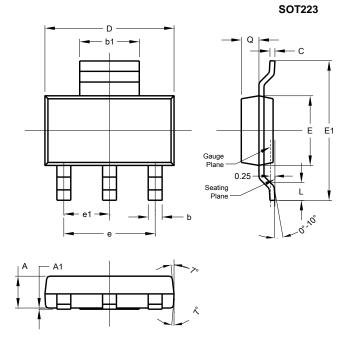
## Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)





## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

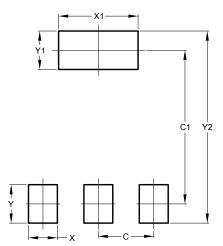


	SOT223					
Dim	Min	Max	Тур			
Α	1.55	1.65	1.60			
A1	0.010	0.15	0.05			
b	0.60	0.80	0.70			
b1	2.90	3.10	3.00			
С	0.20	0.30	0.25			
D	6.45	6.55	6.50			
Е	3.45	3.55	3.50			
E1	6.90	7.10	7.00			
е	-	-	4.60			
e1	-	-	2.30			
L	0.85	1.05	0.95			
Q	0.84	0.94	0.89			
All Dimensions in mm						

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.





Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00



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